

MAXIMUM RATINGS

Symbol	Characteristics	Value	Unit
V_{CC}	DC Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage	$-0.5 \leq V_I \leq +7.0$	V
V_O	DC Output Voltage Output in Z or LOW State (Note 1)	$-0.5 \leq V_O \leq 7.0$	V
I_{IK}	DC Input Diode Current $V_I < GND$	-50	mA
I_{OK}	DC Output Diode Current $V_O < GND$	-50	mA
I_O	DC Output Sink Current	± 50	mA
I_{CC}	DC Supply Current Per Supply Pin	± 100	mA
I_{GND}	DC Ground Current Per Ground Pin	± 100	mA
T_{STG}	Storage Temperature Range	-65 to +150	°C
P_D	Power Dissipation in Still Air SC-88, TSOP-6	200	mW
θ_{JA}	Thermal Resistance SC-88, TSOP-6	333	°C/W
T_L	Lead temperature, 1 mm from case for 10 s	260	°C
T_J	Junction temperature under bias	+150	°C
V_{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V
$I_{Latchup}$	Latchup Performance Above V_{CC} and Below GND at 85°C (Note 5)	± 500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I_O absolute maximum rating must be observed.
2. Tested to EIA/JESD22-A114-A
3. Tested to EIA/JESD22-A115-A
4. Tested to JESD22-C101-A
5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply Voltage Operating Data Retention Only	1.65 1.5	5.5 5.5	V
V_I	Input Voltage	0	5.5	V
V_O	Output Voltage (Z or LOW State)	0	5.5	V
T_A	Operating Free-Air Temperature	-55	+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate $V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$ $V_{CC} = 3.0\text{ V} \pm 0.3\text{ V}$ $V_{CC} = 5.0\text{ V} \pm 0.5\text{ V}$	0 0 0	20 10 5	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-40°C ≤ T _A ≤ 85°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	High-Level Input Voltage		1.65 2.3 to 5.5	0.75 V _{CC} 0.70 V _{CC}			0.75 V _{CC} 0.70 V _{CC}		V
V _{IL}	Low-Level Input Voltage		1.65 2.3 to 5.5			0.25 V _{CC} 0.30 V _{CC}		0.25 V _{CC} 0.30 V _{CC}	V
I _{LKG}	Z-State Output Leakage Current	V _{IN} = V _{IL} V _{OUT} = V _{CC} or GND	1.65 to 5.5			±5.0		±10.0	μA
V _{OL}	Low-Level Output Voltage V _{IN} = V _{IH}	I _{OL} = 100 μA	1.65 to 5.5		0.0	0.1		0.1	V
		I _{OL} = 3 mA	1.65		0.08	0.24			
		I _{OL} = 8 mA	2.3		0.22	0.3		0.3	
		I _{OL} = 12 mA	2.7		0.22	0.4		0.4	
		I _{OL} = 16 mA	3.0		0.28	0.4		0.4	
		I _{OL} = 24 mA	3.0		0.38	0.55		0.55	
		I _{OL} = 32 mA	4.5		0.42	0.55		0.55	
I _{IN}	Input Leakage Current	V _{IN} or V _{OUT} = V _{CC} or GND	0 to 5.5			±0.1		±1.0	μA
I _{OFF}	Power Off-Output Leakage Current	V _{OUT} = 5.5 V	0			1		10	μA
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			1		10	μA

AC ELECTRICAL CHARACTERISTICS t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-40°C ≤ T _A ≤ 85°C		Unit
				Min	Typ	Max	Min	Max	
t _{PZL}	Propagation Delay (Figure 3 and 4)	R _L = R ₁ = 5000 Ω, C _L = 15 pF	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
		R _L = R ₁ = 500 Ω, C _L = 50 pF	2.5 ± 0.20	0.8	3.0	3.6	0.8	4.1	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	3.3 ± 0.30	0.8	2.4	3.2	0.8	3.7	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	5.0 ± 0.50	0.5	2.4	3.0	0.5	3.5	
t _{PLZ}	Propagation Delay (Figure 3 and 4)	R _L = R ₁ = 5000 Ω, C _L = 15 pF	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
		R _L = R ₁ = 500 Ω, C _L = 50 pF	2.5 ± 0.20	0.8	3.0	3.6	0.8	4.1	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	3.3 ± 0.30	0.8	2.1	3.2	0.8	3.7	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	5.0 ± 0.50	0.5	1.2	3.0	0.5	3.5	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	2.5	pF
C _{OUT}	Output Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	4	pF
C _{PD}	Power Dissipation Capacitance (Note 6)	10 MHz, V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	4	pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-55°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	High-Level Input Voltage		1.65 2.3 to 5.5	0.75 V _{CC} 0.70 V _{CC}			0.75 V _{CC} 0.70 V _{CC}		V
V _{IL}	Low-Level Input Voltage		1.65 2.3 to 5.5			0.25 V _{CC} 0.30 V _{CC}		0.25 V _{CC} 0.30 V _{CC}	V
I _{LKG}	Z-State Output Leakage Current	V _{IN} = V _{IL} V _{OUT} = V _{CC} or GND	1.65 to 5.5			±5.0		±10.0	μA
V _{OL}	Low-Level Output Voltage V _{IN} = V _{IH}	I _{OL} = 100 μA	1.65 to 5.5		0.0	0.1		0.1	V
		I _{OL} = 3 mA	1.65		0.08	0.24			
		I _{OL} = 8 mA	2.3		0.22	0.3		0.35	
		I _{OL} = 12 mA	2.7		0.22	0.4		0.45	
		I _{OL} = 16 mA	3.0		0.28	0.4		0.5	
		I _{OL} = 24 mA	3.0		0.38	0.55		0.65	
		I _{OL} = 32 mA	4.5		0.42	0.55		0.65	
I _{IN}	Input Leakage Current	V _{IN} or V _{OUT} = V _{CC} or GND	0 to 5.5			±0.1		±1.0	μA
I _{OFF}	Power Off-Output Leakage Current	V _{OUT} = 5.5 V	0			1		10	μA
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			1		10	μA

AC ELECTRICAL CHARACTERISTICS t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-55°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
t _{PZL}	Propagation Delay (Figure 3 and 4)	R _L = R ₁ = 5000 Ω, C _L = 15 pF	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
		R _L = R ₁ = 500 Ω, C _L = 50 pF	2.5 ± 0.20	0.8	3.0	3.6	0.8	4.1	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	3.3 ± 0.30	0.8	2.4	3.2	0.8	3.7	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	5.0 ± 0.50	0.5	2.4	3.0	0.5	3.5	
t _{PLZ}	Propagation Delay (Figure 3 and 4)	R _L = R ₁ = 5000 Ω, C _L = 15 pF	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
		R _L = R ₁ = 500 Ω, C _L = 50 pF	2.5 ± 0.20	0.8	3.8	4.5	0.8	5.0	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	3.3 ± 0.30	0.8	2.9	3.2	0.8	3.7	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	5.0 ± 0.50	0.5	1.2	3.0	0.5	3.5	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	2.5	pF
C _{OUT}	Output Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	4	pF
C _{PD}	Power Dissipation Capacitance (Note 6)	10 MHz, V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	4	pF

7. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

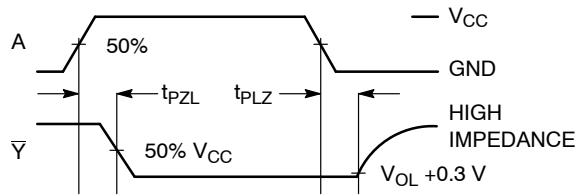
NL27WZ06

Figure 3. Switching Waveforms

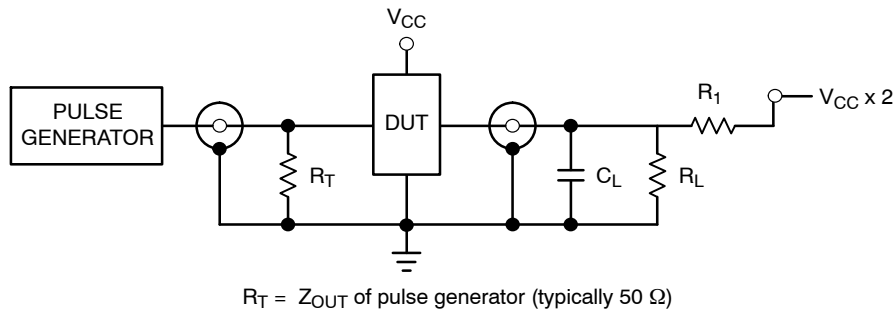


Figure 4. Test Circuit

ORDERING INFORMATION

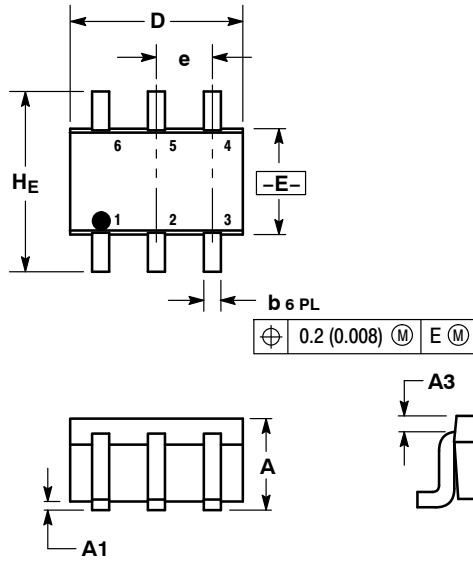
Device	Package	Shipping [†]
NL27WZ06DFT2	SC-88	3000 / Tape & Reel
NL27WZ06DFT2G	SC-88 (Pb-Free)	
NL27WZ06DTT1	TSOP-6	
NL27WZ06DTT1G	TSOP-6 (Pb-Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NL27WZ06

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE W

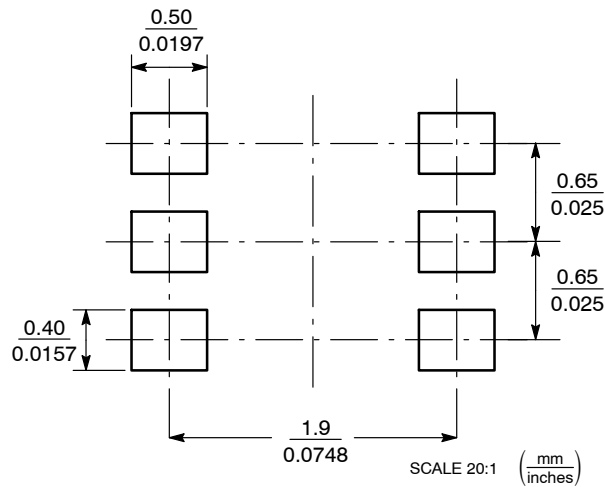


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H _E	2.00	2.10	2.20	0.078	0.082	0.086

SOLDERING FOOTPRINT*

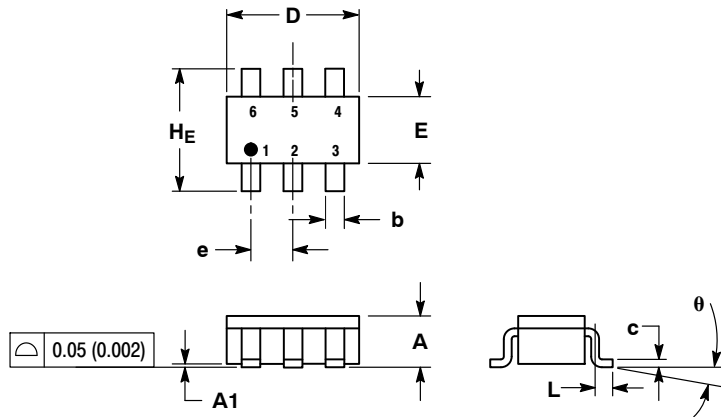


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 ISSUE T

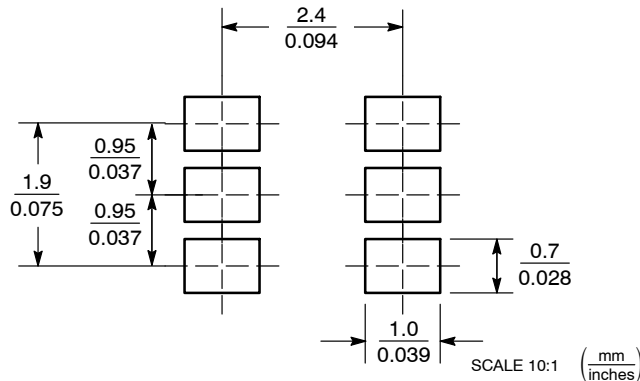


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.38	0.50	0.010	0.014	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	—	10°	0°	—	10°

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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